**Product data sheet** 

# 1. General description

Ultrafast power diode in a TO252 (DPAK) plastic package.





### 2. Features and benefits

- · Fast switching
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT
- Package meets UL94V0 which guaranteed by Epoxy Mold Compound

## 3. Applications

- · Active PFC in air conditioner
- High frequency switched-mode power supplies
- Power Factor Correction (PFC)

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage				V		
I <sub>F(AV)</sub>	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 136$ °C; Fig. 1; Fig. 2; Fig. 3				Α	
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 136 °C; square-wave pulse		30			Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		140			Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		154			Α
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.75	2.40	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.35	2.00	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	26	-	ns

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected		K <b>_ L/</b> _ A
2	K	cathode [1]		K —— A 001aaa020
3	А	anode		
mb	К	mounting base; connected to cathode		

<sup>[1]</sup> It is not possible to connect to pin 2 of the TO252 package.

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV15MD-650P	TO252	BYV15MD-650PJ	Reel	2500	TO252d	07-Sep-2022

# 7. Marking

### Table 4. Marking codes

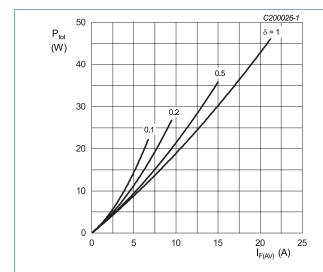
Type number	Marking codes
BYV15MD-650P	BYV15MD 650P

# 8. Limiting values

### Table 5. Limiting values

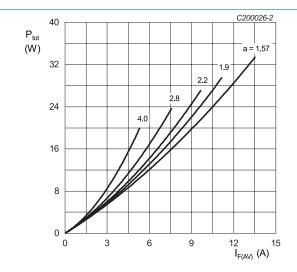
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			650	V
$V_{\text{RWM}}$	crest working reverse voltage			650	V
$V_R$	reverse voltage	DC		650	V
I <sub>F(AV)</sub>	average forward current	$δ$ = 0.5 ; square-wave pulse; $T_{mb} \le 136$ °C; Fig. 1; Fig. 2; Fig. 3		15	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 136 °C; square-wave pulse		30	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		140	Α
		$t_p = 8.3 \text{ ms}; T_{j(init)} = 25 \text{ °C}; \text{ sine-wave pulse}$		154	Α
T <sub>stg</sub>	storage temperature			-65 to 175	°C
T <sub>j</sub>	junction temperature			-65 to 175	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$  $V_o = 1.643 \text{ V}; R_s = 0.0249 \Omega$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.643 V;  $R_s$  = 0.0249  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

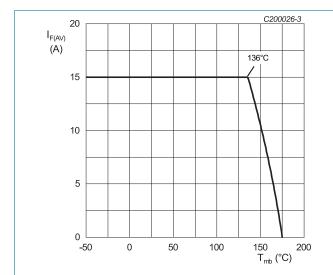


Fig. 3. Forward current as a function of mounting base temperature; maximum values

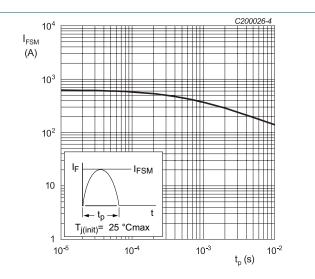


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5		-	-	1.1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	[2]	-	50	-	K/W

[2] Device mounted on an FR4 PCB, single-sided copper, tin plated and standard footprint.

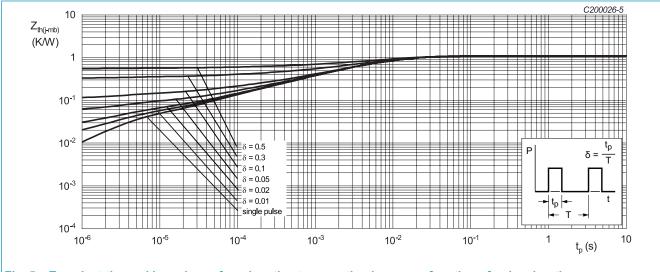
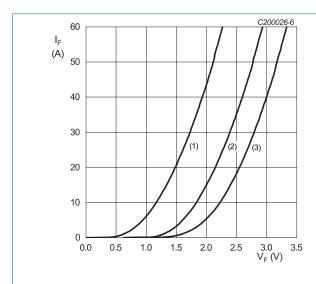


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

# 10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.75	2.40	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.35	2.00	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.5	30	μΑ
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	-	8.0	mA
Dynamic	characteristics				1		
Q <sub>r</sub>	reverse charge	$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	80	-	nC
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	330	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{rr} = 0.25 \text{ A}; T_j = 25 \text{ °C}$		-	28	-	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	26	-	ns
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	45	-	ns
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	85	-	ns
I <sub>RM</sub>	peak reverse recovery currentnon-repetitive	$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	3.5	-	А
	avalanche energy	$I_F$ = 15 A; $V_R$ = 200 V; $dI_F/dt$ = 200 A/ $\mu$ s; $T_j$ = 125 °C; Fig. 7		-	7.2	-	А
E <sub>as</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		16.8	-	-	mJ



 $V_o$  = 1.643 V;  $R_s$  = 0.0249  $\Omega$ 

(1)  $T_j = 150 \,^{\circ}\text{C}$ ; typical values (2)  $T_j = 150 \,^{\circ}\text{C}$ ; maximum values (3)  $T_j = 25 \,^{\circ}\text{C}$ ; maximum values



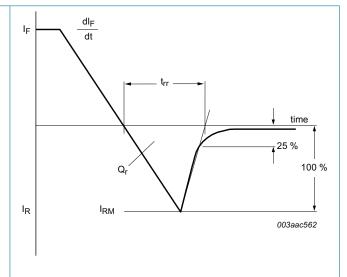
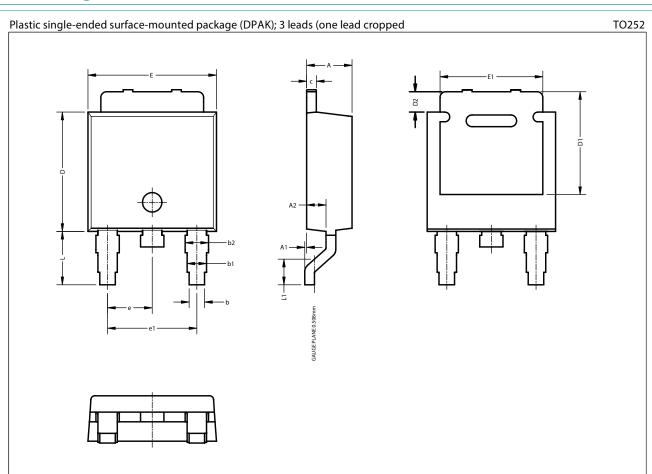


Fig. 7. Reverse recovery definitions; ramp recovery

# 11. Package outline



#### Note:

1. All dimensions do not include mold flash & gate remain and metal protrusion.

Unit	t	Α	A1	A2	b	b1	b2	С	D	D1	D2	Е	E1	е	e1	L	L1
mm no		2.16	0.00	0.90	0.70	0.86	1.06	0.46	5.97	5.05	0.98	6.45	5.20	2.30	4.60	2.60	1.25
		2.41	0.10	1.10	0.90	1.11	1.32	0.58	6.22	5.35	1.18	6.75				2.90	1.65

### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**BYV15MD-650P** 

Ultrafast power diode

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## 13. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
	Limiting values	
9.	Thermal characteristics	5
10	Characteristics	6
11	. Package outline	7
	Legal information	
	3. Contents	

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